Reg. No. :						
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Question Paper Code: 37043

B.E. / B.Tech. DEGREE EXAMINATION, NOV 2017

Seventh Semester

Electronics and Communication Engineering

01UEC703 - MICROWAVE ENGINEERING

(Regulation 2013)

Duration: Three hours Maximum: 100 Marks

Answer ALL Questions

PART A -
$$(10 \times 2 = 20 \text{ Marks})$$

- 1. State the differences between isolator and circulator.
- 2. Mention the reason for using S-matrix for microwave analysis.
- 3. What are the factors reducing efficiency of IMPATT diode?
- 4. Define negative resistance.
- 5. Why magnetron is called as cross filed device?
- 6. Compare TWTA and klystron amplifier.
- 7. Outline the features of coplanar strip line and microstrip line?
- 8. Write about diffusion and ion implantation process in fabrication.
- 9. List the different types of impedance measurement methods.
- 10. Define insertion loss.

PART - B (5 x
$$16 = 80 \text{ Marks}$$
)

11. (a) Explain different types of waveguide junction with neat diagram. (16)

Or

(16)

(b) Describe the scattering matrix of a directional coupler.

12.	(a)	Explain the various modes of operation of Gunn oscillator with neat sketches. ((16)
		Or	
	(b)	Derive the Manley Rowe power relations for the parametric amplifier.	(16)
13.	(a)	Explain the velocity modulation process and derive the condition at which maxim bunching occurs in two cavity klystron.	num (16)
		Or	
	(b)	Describe with a neat sketch, the constructional details and principle of operation two cavity Klystron tube. Derive the expression for beam current and efficiency.	n of
			(16)
14.	(a)	Discuss the various losses of microstrip line in detail and derive the q-factor microstrip lines.	r of (16)
		Or	
	(b)	Explain in detail with suitable diagrams, the fabrication techniques of a monoli microwave integrated circuit.	thic (16)
15.	(a)	Explain in detail the various impedance measurement techniques.	(16)
		Or	
	(b)	Describe in detail with block diagram, the measurement of VSWR.	(16)